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(54) Title: MULTI JUNCTIONS IN A SEMICONDUCTOR DEVICE FORMED BY DIFFERENT DEPOSITION TECHNIQUES

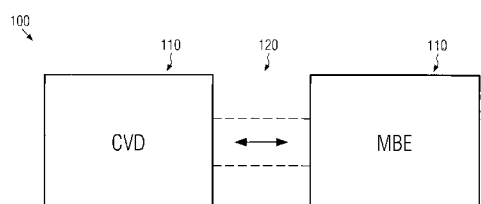


FIG. 1a

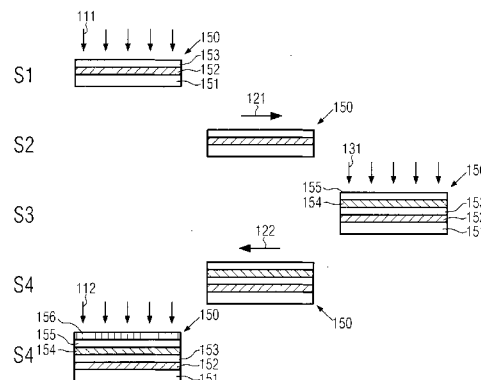


FIG. 1b

(57) Abstract: A semiconductor device, in particular a solar cell (450) is formed on the basis of a hybrid deposition strategy using MOCVD and MBE in order to provide lattice matched semiconductor compounds (452, 453, 454). To this end, the MBE may be applied for providing a nitrogen-containing semiconductor compound (453) that allows a desired low band gap energy and a lattice matched configuration with respect to gallium arsenide substrates.